

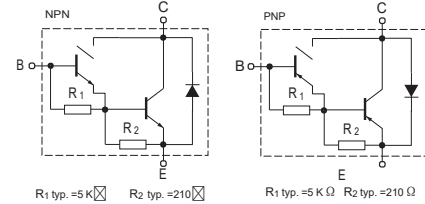
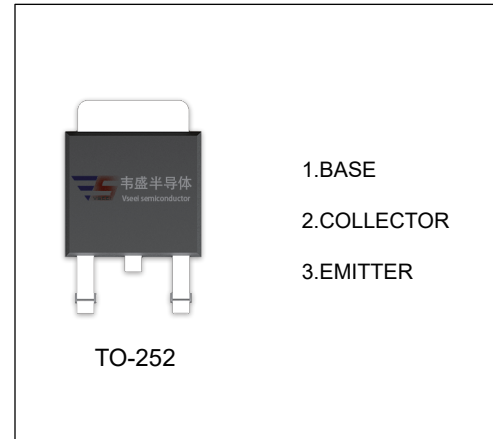
MJD127 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Electrically Similar to Popular TIP127
- Built-in a Damper Diode at E-C

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-100	V
V _{CE0}	Collector-Emitter Voltage	-100	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-8	A
P _C	Collector Power Dissipation	1.5	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-30mA, I _B =0	-100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-100V, I _E =0			-10	μ A
Collector-emitter cut-off current	I _{CEO}	V _{CE} =-50V, I _B =0			-10	μ A
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-2	mA
DC current gain	h _{FE(1)}	V _{CE} =-4V, I _C =-4A	1000		12000	
	h _{FE(2)}	V _{CE} =-4V, I _C =-8A	100			
Collector-emitter saturation voltage	V _{CE(sat) 1*}	I _C =-4A, I _B =-16mA			-2	V
	V _{CE(sat) 2*}	I _C =-8A, I _B =-80mA			-4	V
Base-emitter saturation voltage	V _{BE(sat) *}	I _C =-8A, I _B =-80mA			-4.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-4V, I _C =-4A			-2.8	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=0.1MHz			300	pF

*Pulse Test: Pulse Width \leq 380 μ s, Duty Cycle \leq 2%

Typical Characteristics

MJD127

